(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property Organization
International Bureau

(43) International Publication Date
22 July 2004 (22.07.2004)

PCT

(10) International Publication Number
WO 2004/061943 A1

(51) International Patent Classification[7]: H01L 21/762

(21) International Application Number:
PCT/IB2004/000285

(22) International Filing Date: 7 January 2004 (07.01.2004)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:

0300098	7 January 2003 (07.01.2003)	FR
60/472,470	22 May 2003 (22.05.2003)	US

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(81) Designated States *(unless otherwise indicated, for every kind of national protection available)*: AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NA, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM, ZW.

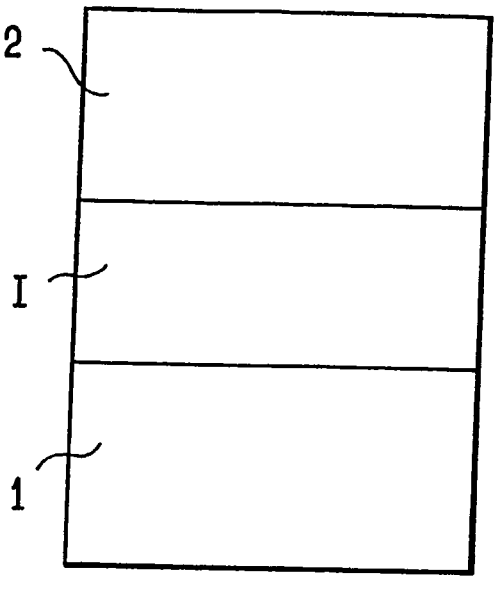
(84) Designated States *(unless otherwise indicated, for every kind of regional protection available)*: ARIPO (BW, GH, GM, KE, LS, MW, MZ, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IT, LU, MC, NL, PT, RO, SE, SI, SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

Declaration under Rule 4.17:
— *of inventorship (Rule 4.17(iv)) for US only*

Published:
— *with international search report*

[Continued on next page]

(54) Title: RECYCLING BY MECHANICAL MEANS OF A WAFER COMPRISING A TAKING-OFF STRUCTURE AFTER TAKING-OFF A THIN LAYER THEREOF



(57) Abstract: Method of recycling a donor wafer (10) after having taken off a useful layer comprising a material chosen from semiconductor materials. The donor wafer (10) comprising successively a substrate (1) and a taking-off structure (I), the taking-off structure (I) before taking-off comprising the useful layer to take off; The method comprising removal of substance on the side where the taking-off took place, characterized in that the removal of substance comprises employing mechanical means so that, after removal of substance, at least a part of the taking-off structure (I') remains, this at least part of the taking-off structure (I') including at least one other useful layer that can be taken off after recycling, without a supplementary step of reforming a useful layer. The present document likewise relates to: -methods of taking-off a thin layer from a donor wafer (10) which may be recycled according to the invention; -donor wafer (10) which may be recycled according to the invention.

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— *before the expiration of the time limit for amending the claims and to be republished in the event of receipt of amendments*

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